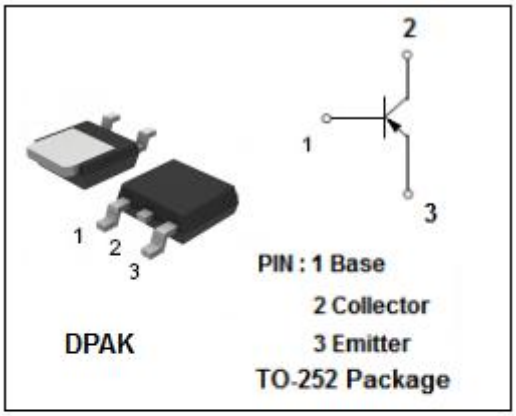
isc Silicon PNP Power Transistor — 2SB962-Z

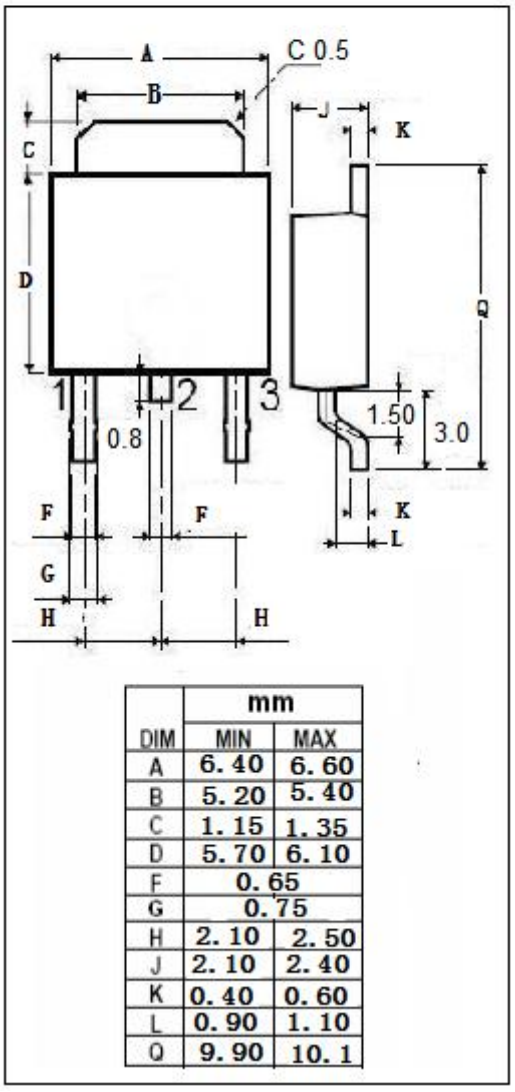


DESCRIPTION

- Low Collector Saturation Voltage
  : $V_{CE(sat)}$= -0.3V(Typ)@I_C= -2.0A
- PNP silicon epitaxial transistor
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- The 2SB962-Z is designed for Audio frequency amplifier and switching ,especially in hybrid integrated circuits



DIM	mm MIN	MAX
A	6.40	6.60
B	5.20	5.40
C	1.15	1.35
D	5.70	6.10
F	0.65	
G	0.75	
H	2.10	2.50
J	2.10	2.40
K	0.40	0.60
L	0.90	1.10
Q	9.90	10.1

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-3	A
I_{CP}	Collector Current-Pulse	-6	A
P_C	Total Power Dissipation @ Ta=25℃	2.0	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{CE(sat)}$NOTE	Collector-Emitter Saturation Voltage	I_C= -2.0A; I_B= -200mA		-0.3	-0.5	V
$V_{BE(sat)}$NOTE	Base-Emitter Saturation Voltage	I_C= -2.0A; I_B= -200mA		-1.0	-2.0	V
I_{EBO}	Emitter Cutoff Current	V_{EB}= -3V; I_C= 0			-1.0	μA
I_{CBO}	Collector Cutoff Current	V_{CB}= -30V; I_E= 0			-10	μA
h_{FE1}NOTE	DC Current Gain	I_C= -1A; V_{CE}= -2V	60		400	
h_{FE2}NOTE	DC Current Gain	I_C= -20mA; V_{CE}= -2V	30			
fT	Transition frequency	V_{CE}=-5V ,I_C=-100mA		80		MHz
Cob	Collector output capacitance	V_{CB}=-10V ,I_E=0,f=1MHz		55		pF

NOTE:Pulse test PW≤350us,duty cycle ≤2%

◆ **h_{FE1} Classifications**

R	Q	P	E
60-120	100-200	160-320	200-400